

IN THE SPECIFICATION:

Please replace paragraph number [0001] with the following rewritten paragraph:

[0001] This application is a continuation of application Serial No. 09/495,143, filed January 31, 2000, ~~pending~~ now U.S. Patent 6,655,234, issued December 2, 2003.

Please replace paragraph number [0049] with the following rewritten paragraph:

[0049] The preferred method of the invention is outlined in FIGS. 17, 18 and 19, and illustrates the difficulties overcome by the present invention in manufacturing cavitated cutting elements 20, 910 of the previous ~~figures~~ FIGS. 1 through 16, as well as others not shown.

Please replace paragraph number [0055] with the following rewritten paragraph:

[0055] As illustrated in FIG. 19D, a layer 84 of particulate diamond crystals is placed atop substrate 34, and the loaded receptacle or cell 80 is subjected to a HTHP process schematically shown in FIG. 17. For example, a ram 88 may be used to compress the diamond layer 84 and substrate 34 at high temperature to form a superabrasive diamond ~~layer, or table, 30~~ layer or table 30 (shown in FIG. 19E) securely bonded to the upper surface 72 of substrate 34. If desired, a metal catalyst, not shown, may be included to enhance the table formation and bonding strength.